

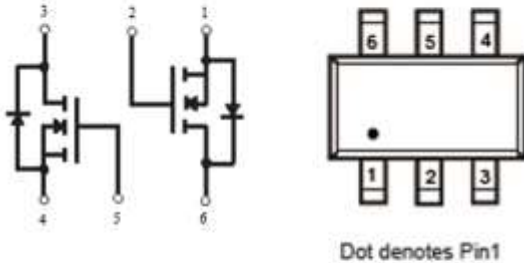
N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 60V
- I_D 340mA
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <2.5ohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <3.0ohm

General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage



Dot denotes Pin1

SOT-363

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	60	V
Gate-source Voltage	V_{GS}	± 30	V
Peak Gate-source Voltage $T_p < 50\mu s$, duty cycle=0.25	V_{GSm}	± 40	V
Drain Current	I_D	$T_A=25^\circ C$ @ Steady State	340
		$T_A=70^\circ C$ @ Steady State	272
Pulsed Drain Current ^A	I_{DM}	1.5	A
Total Power Dissipation @ $T_A=25^\circ C$	P_D	350	mW
Thermal Resistance Junction-to-Ambient @ Steady State ^B	$R_{\theta JA}$	357	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
2N7002DW	F2	K72	3000	30000	120000	7" reel

2N7002DW

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS1}	V _{GS} = ±30V, V _{DS} =0V			±100	nA
	I _{GSS2}	V _{GS} = ±20V, V _{DS} =0V			±50	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1	1.6	2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D =300mA		1.2	2.5	Ω
		V _{GS} = 4.5V, I _D =200mA		1.3	3.0	
Diode Forward Voltage	V _{SD}	I _S =300mA, V _{GS} =0V			1.2	V
Maximum Body-Diode Continuous Current	I _S				340	mA
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f=1MHZ		15		pF
Output Capacitance	C _{oss}			9.5		
Reverse Transfer Capacitance	C _{rss}			5.5		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =15V, V _{DS} =30V, I _D =0.3A		1.7	2.4	nC
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =30V, I _D =300mA, R _{GEN} =6Ω		5		ns
Turn-off Delay Time	t _{D(off)}			17		
Reverse recovery Time	t _{rr}	V _{GS} =0V, I _S =300mA, V _R =25V, di _S /dt=- 100A/μs		30		ns

A. Pulse Test: Pulse Width ≤300us, Duty cycle ≤2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

■ Typical Performance Characteristics

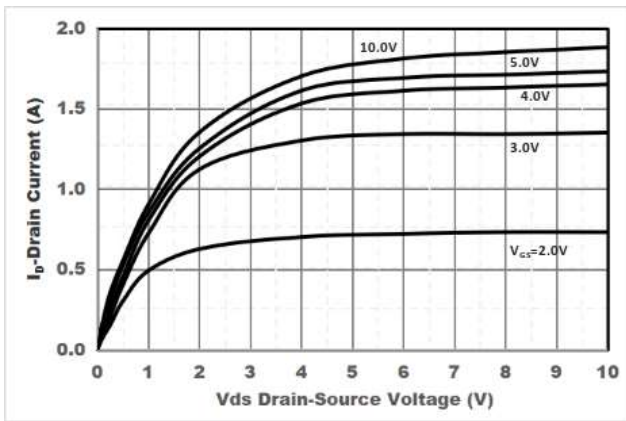


Figure1. Output Characteristics

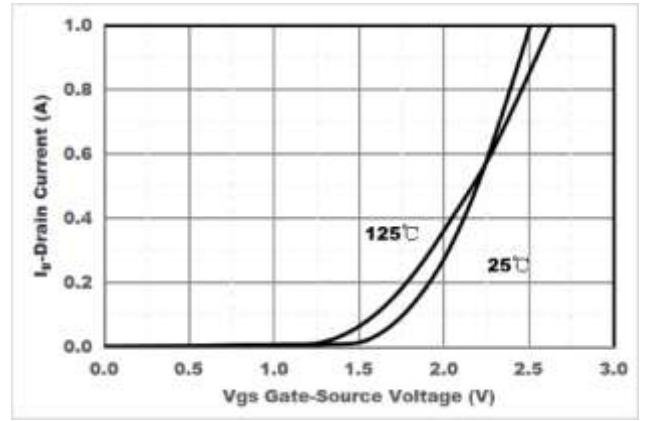


Figure2. Transfer Characteristics

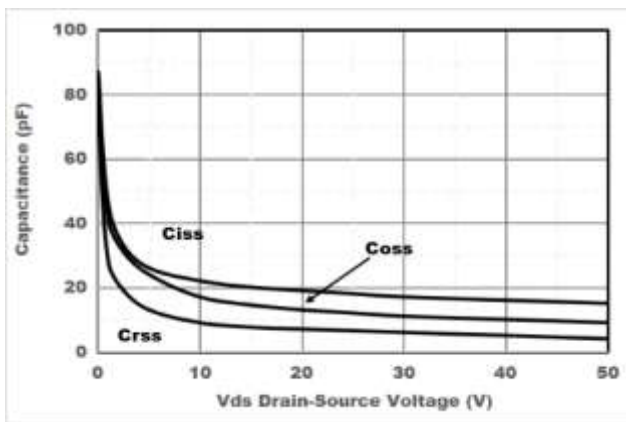


Figure3. Capacitance Characteristics

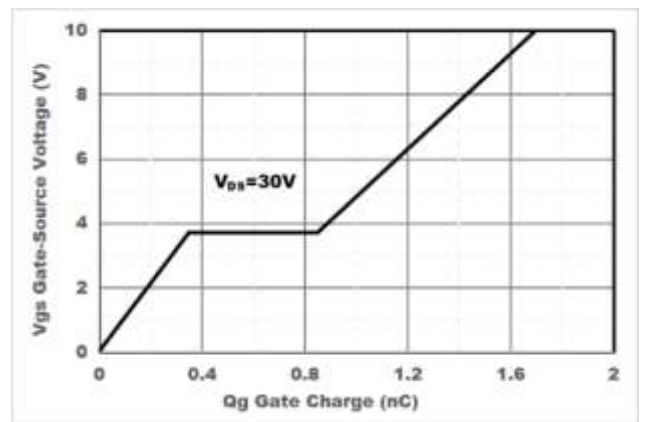


Figure4. Gate Charge

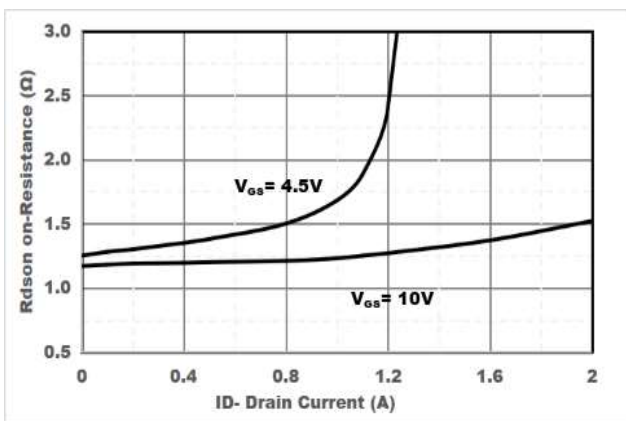


Figure5. Drain-Source on Resistance

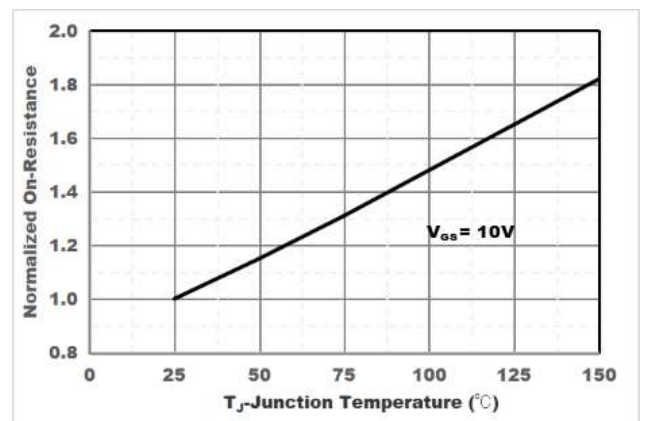


Figure6. Drain-Source on Resistance

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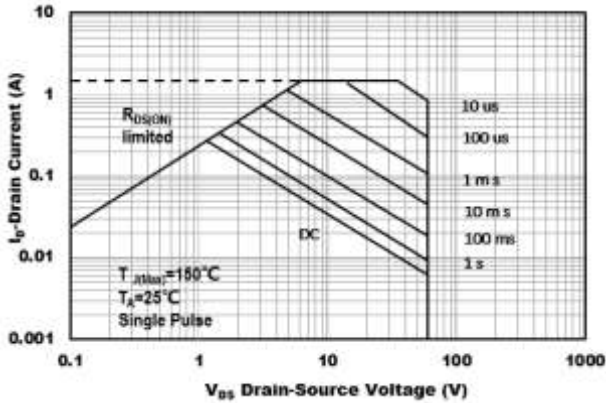


Figure7. Safe Operation Area

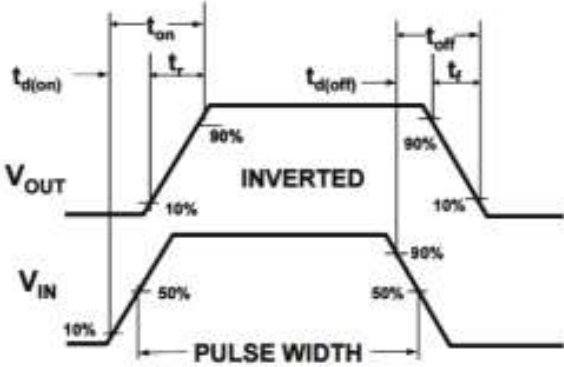
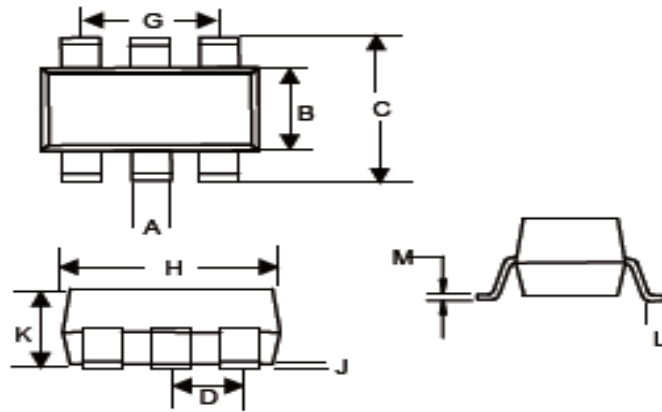


Figure8. Switching wave

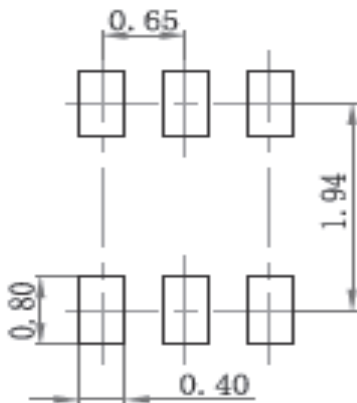
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■ SOT-363 Package information



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.006	0.014	0.15	0.35	
B	0.045	0.053	1.15	1.35	
C	0.079	0.096	2.00	2.45	
D	0.026		0.65		TYP.
G	0.047	0.055	1.20	1.40	
H	0.071	0.087	1.80	2.20	
J	----	0.004	----	0.10	
K	0.031	0.043	0.80	1.10	
L	0.010	0.018	0.26	0.46	
M	0.003	0.006	0.08	0.15	

SUGGESTED SOLDER PAD LAYOUT



2N7002DW

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